

# EUROPEAN NANOELECTRONICS INFRASTRUCTURE FOR INNOVATION



G.Casanova CAPA 23/10/13

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## Objectives/Activities

- Infrastructure for Innovation (ENI2) is designed to create mid- and long- term technology roadmaps for cooperative (3-6-9 years) R&D&I projects in nanoelectronics and to establish strategic groupings of research communities with common interests.
- To set-up « large federative projects » of European interest for technology prototyping and demonstrations.



# eni<sup>2</sup> 's ambition: being a 2 way bridge between academic knowledge and marketable products by industry

In nanoelectronics, a successful innovative infrastructure will rely to a three R&D levels organization



#### **ACADEMIC LABORATORIES**

 Basic understanding, test and validation of innovative architectures, materials and processes in order to identify the most promising topics for future ICT



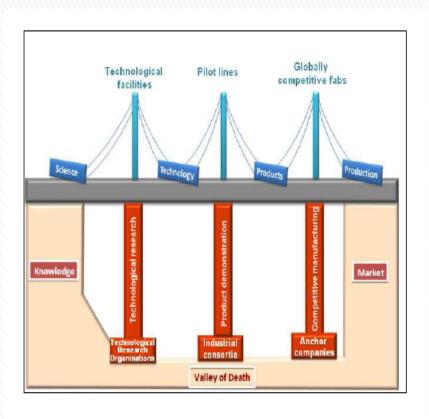
#### **INSTITUTES (Integration Centers)**

 Technology implementation and performance assessment on R&D equipments; development of high performance Logic, Memories, Derivative, Power devices



#### **INDUSTRIALISTS**

Technology exploitation as functional product, process optimization, yield, product reliability, device and interconnect architecture and design



Innovation crosses the bridge from left to right but it's a 2 way bridge meaning there is a feedback loop to academics

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## **ENI2 MEMBERS**

INSTITUT POLYTECHNIQUE DE GRENOBLE	FRANCE
CONSORZIO NAZIONALE INTERUNIVERSITARIO PER LA NANOELETTRONICA	ITALY
COMMISSARIAT A L ENERGIE ATOMIQUE ET AUX ENERGIES ALTERNATIVES	FRANCE
ASM INTERNATIONAL N.V.	THE NETHERLANDS
CIRCUITS MULTI-PROJETS	FRANCE
FRAUNHOFER-GESELLSCHAFT ZUR FOERDERUNG DER ANGEWANDTEN	GERMANY
FORSCHUNG E.V	
INTERUNIVERSITAIR MICRO-ELECTRONICA CENTRUM VZW	BELGIUM
AIT AUSTRIAN INSTITUTE OF TECHNOLOGY GMBH	AUSTRIA
AGENCIA ESTATAL CONSEJO SUPERIOR DE INVESTIGACIONES CIENTIFICAS	SPAIN
ECOLE POLYTECHNIQUE FEDERALE DE LAUSANNE	SWITZERLAND
EDACENTRUM GMBH	GERMANY
FORSCHUNGSZENTRUM JUELICH GMBH	GERMANY
ION BEAM SERVICES	FRANCE
CATALAN INSTITUTE OF NANOTECHNOLOGY	SPAIN
INFINEON TECHNOLOGIES AG	GERMANY
INSTYTUT TECHNOLOGII ELEKTRONOWEJ	POLAND
KUNGLIGA TEKNISKA HOEGSKOLAN	SWEEDEN
MICRON SEMICONDUCTOR ITALIA SRL	ITALY
NATIONAL CENTER FOR SCIENTIFIC RESEARCH "DEMOKRITOS"	GREECE
THALES SA	FRANCE

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NXP SEMICONDUCTORS BELGIUM NV	BELGIUM
OPEN ENGINEERING	BELGIUM
INSTITUT SINANO ASSOCIATION	FRANCE
STIFTELSEN SINTEF	NORWAY
STMICROELECTRONICS S.A.	FRANCE
THYIA TEHNOLOGIJE D.O.O	SLOVENIA
TECHNISCHE UNIVERSITEIT DELFT	THE NETHERLANDS
NEDERLANDSE ORGANISATIE VOOR TOEGEPAST	THE NETHERLANDS
NATUURWETENSCHAPPELIJK ONDERZOEK - TNO	
UNIVERSITY COLLEGE CORK, NATIONAL UNIVERSITY OF IRELAND, CORK	IRELAND
UNIVERSITE CATHOLIQUE DE LOUVAIN	BELGIUM
UPPSALA UNIVERSITET	SWEDEN
TEKNOLOGIAN TUTKIMUSKESKUS VTT	FINLAND
TECHNISCHE UNIVERSITEIT EINDHOVEN	THE NETHERLANDS
TUBITAK	TURKEY
INSTITUTO DE TELECOMUNICACOES	PORTUGAL
UNIVERSITY OF BRADFORD	UNITED KINGDOM
COMMONWEALTH ITU Group	UNITED KINGDOM
IMT BUCHAREST	ROMANIA
INSTITUTE OF TECHNICAL PHYSICS AND MATERIALS SCIENCE	HUNGRIA
SLOVAK UNIVERSITY OF TECHNOLOGY	SLOVAKIA
WROCLAY UNIVERSITY OF TECHNOLOGY	POLAND

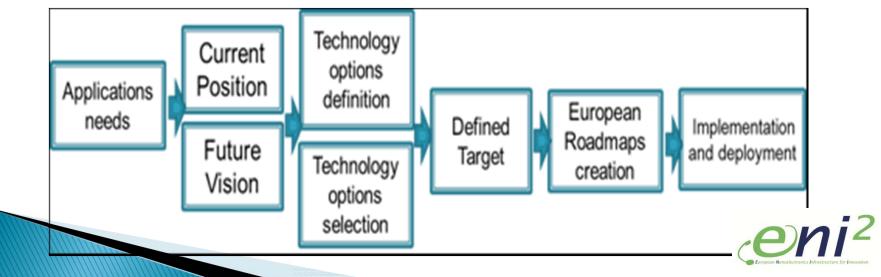
### **METHODOLOGY**

- Applications needs
- Research Domains
- Template
- Road-mapping activities
- Who is doing what
- Long-term Program/concrete case

#### **TECHNOLOGY ROADMAPPING**

For the technological domains (nanoscale FET, Smart energy and Smart sensors), we have agreed on the following road mapping process:

- (1) **Identify the "Applications**" that will be the focus of the roadmap.
- (2)Explain the state of the art and the vision. (3) Define the technology options and select the areas of cooperation to be addressed at European level (4) Create the roadmaps by specifying the major technology areas (devices, interconnect, materials.....) and associated targets (6) Generate and implement a plan to develop and deploy Long term Programmes.



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# Applications needs

- Nanoscale FET (Set Top Box, Smartphones, HPC, mini-servers);
- Smart Energy (smart grid, electrical cars).
- Smart sensors (Internet of things, e-health).
- Heterogeneous integration to offer greater functionality at lower cost.
- -For improving performance of interconnect: Computing (mini-server, APs, HPC)
- For improving the form factor (smaller volume) : Interfaces ( Haptic, Sensors, Hearing aids)
- For demonstrating heterogeneous integration and modularity: Smart energy

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# Selection of five short to long-term research programs



## NANOSCALE FET



**SMART ENERGY** 



**SMART SENSORS** 



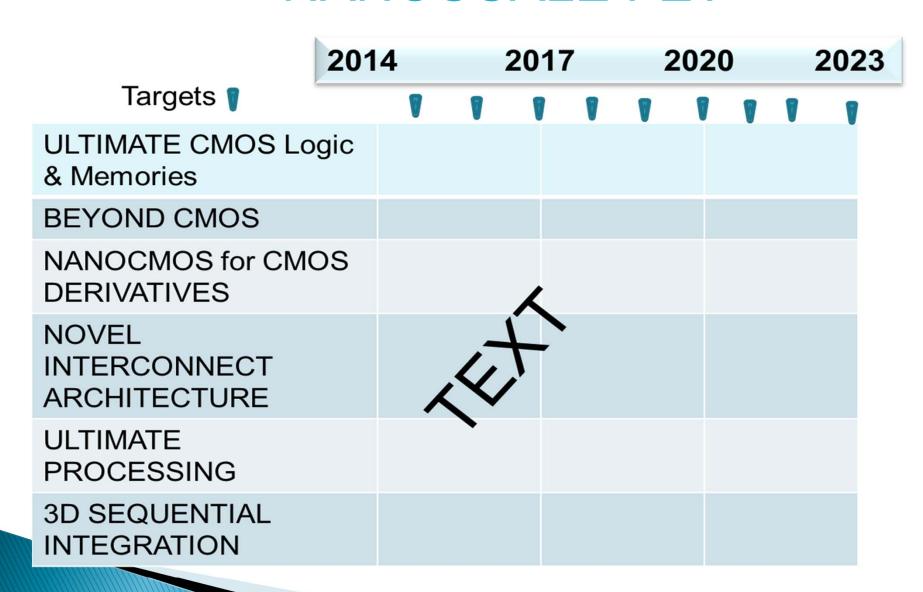


# Driving the execution

Role	Company	Name
Project Manager	ST	G.Casanova
Steering Committee	Sinano-IUNET- CEA/Leti-ASM-FHG- NXP-IFX-ST- IMEC	F.Balestra- E.Sangiorgi -J.Pelka - B.Van Nooten - W.Dettmann- P.Pype -G.Casanova- A.Van den Bosch
<b>Project Team</b>	Core Group	Annexe
Team Leads	TUDelft-STE-Thales- TUE-ST-NXP-IFX- Sinano-FHG-KTH- CMP-Tyndall-IMEC - STE	M.Graef-P.Blouet- J.P.N Haagh - G.Thomas-M.Ostling -A.Bouffioux F.Balestra - J.Pelka- B.Courtois- A.Mathewson - A.Van den Bosch C.Reita
<b>Executive Sponsors</b>	Aeneas-Catrene offices	

ENI2 Expression of Interest	form	
Nanoscale FET  Areas of collaboration	Potential contribution Yes/no	Priority level (*)
Properties of materials and devices built at the nanoscale		
Modeling of properties of materials and devices		
Multi-physics and multi-scale modeling methodologies		
Novel materials and new functionalities		
New device architectures		5
Novel interconnects architectures		
Development of ultimate processing technologies		
Nano devices for adding new functionalities to CMOS		
Physical and electrical nano characterization		
Integration of very high densities of nano devices		
Other suggested collaboration area	as	

## NANOSCALE FET



## **Smart Energy**

The "Smart energy" wording has been defined as referring to a peculiar technology which combines the integration of high-V / high-I devices with "smart" features capabilities and new materials, in order to provide high efficient all-in-one "power", in System-on-Chip (SoC) or System-in-Package (SiP) forms.

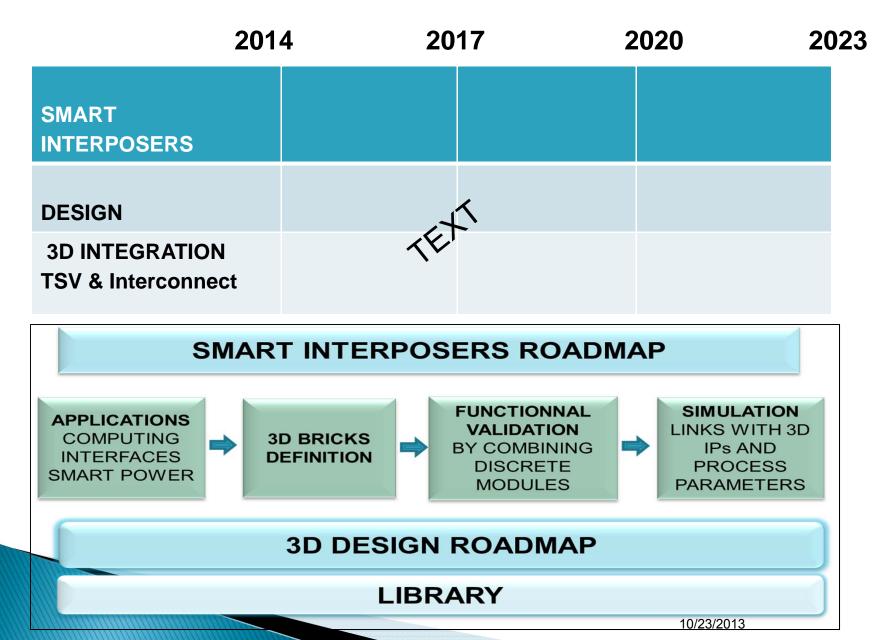
ResearchTopics	< 3 years	3-6 years	>6 years
1.COMPOUND MATERIALS			
2. INTEGRATION OF SMART AND POWER			
3. SMART SYSTEM/MODULE INTEGRATION			
4. POWER TECHNOLOGIES			
5. DESIGN METHODOLOGIES			

## **Smart Sensors**

Smart sensor will rely on various heterogeneous technologies like analogue, digital and RF (Radio Frequency) electronics, MEMS (Micro Electro Mechanical System) coupled with photonics for energy scavenging and integrated chemical batteries. It may also rely on fluidics, pneumatics, optics, chemical, biochemical or mechanics for the transport of the sample to analyze and for its characterization.

ResearchTopics	< 3 years	3-6 years	>6 years
1. NEW GENERATION OF SENSORS (gas, biosensors)			
2. ULTRA LOW POWER NETWORK			
3.SMART SENSORS INTEGRATION			
4. MATERIALS AND PROCESSES			
5. OTHER			

### HETEROGENEOUS INTEGRATION



#### PINOCIONE OF THE INAMOSCALETET LIMIZ ECOSTSTEIN COMMUNICION OF COMMUNICATION

#### **DIFFERENT RESERARCH HORIZON**

	ULTIMATE CMOS	BEYOND CMOS	NOVEL INTERCONNECTS ARCHITECTURES	ULTIMATE PROCESSES TECHNOLOGIES	3D SEQUENTIAL INTEGRATION
	Tyndall	Tyndall	TU Delft	VTT	
	FZ Julich	Univ. Stuttggart	Tyndall	Tyndall	
	luNET	IuNET	Grenoble INP	Grenoble INP	
	Univ.Granada	Univ.Granada	FZ Julich	FZ Julich	
	IMEL	IMEL	Uppsala Univ.	Uppsala Univ.	
	Uppsala Univ.	Uppsala Univ.		KTH	
	Newcastle Univ.	Newcastle Univ.		CNM	
	Univ. Twente	Univ Twente		IMEL	
	URV	URV		TUBITAK	
	Grenoble INP	Grenoble INP			
	UCL	UCL			
ACADEMICS	Warwick Univ	KTH			
	Univ. Glasgow	Univ. Glasgow			
	CNM	CNM			
	IEMN	TU Delft			To be
	IES	VTT			consolidated in
	Chalmers	ICN			Q4
	VTT	TUBITAK			<b>−</b>
	TU Delft				
	ICN				
	TUBITAK				
	KTH				
	FHG	FHG	IMEC	IMEC	Leti
INICTITUTES	ITE	ITE			
INSTITUTES	Leti	Leti	Leti	Leti	
	IMEC	IMEC		FHG	
	ST	ST	ST	ST	ST
INDUCTORALICE	Thales	Thales	Thales	ASM	
INDUSTRIALIST	Micron	Micron		IBS	
		NXP		10/23/201	3

# Example of inputs collection in Smart Energy

# Materials & Processes / Power Production Technologies

Smart energy Areas of collaboration	#	IFX	ST	CEA	TND	CNM	TUD	=	SIN	<b>UCL</b>	ТНА	OCC	F- IISB	UPU	2	TTV	LQAT	ICB
Materials and Processes																		
New materials for high Power semiconductors (SiC, GaN, Saphir, Diamond) and associated manufacturing processes (Homo-hetero-localized epitaxy, characterization and test)		1	1	1	2	1	1	2	1	N	1	1	1	1	1	2	N	1
On SOI medium power technologies	8	1	1	3		N	3	N	1	Ν	N		N	2	2	1		
Low power Mixed analog technologies	8	2	2	N (*)		N	2	1	1	1	N		N	N	1	Ν	1	
Low power RF technologies	11	2	1	N (*)		N	2	1	2	1	N		N	2	1	1	1	1
New materials and associated processes for Smart derivatives compatible with power	8	1	2	N	3	1		N	1	N	2		N	N	1	3	N	П
New materials for large passive capacitors and inductors (high power, high frequency) used together with semiconductors in power conversion		N	2	3	1	N		N	1	N	1	1	1	2	2	2	N	
Logic with HV applications and embedded flash: shrink path & HV properties (40100V)	7	1	1	N		1		N	2	N	3		2	N	2		N	

Smart energy Areas of collaboration		IFX	ST	CEA	TND	CNM	TUD	ITE	SIN	NCL	ТНА	ncc	F- IISB	UPU	2	VTT	LQAT	ICB
Power production technologies	0																	
300mm power production (process, metrology, materials, infrastructure)	7	1	1	2		N		N	2	N	N		2	N	2	N	N	1

# Architectures & System Module../ Methodology & Tools

Smart energy Areas of collaboration		IFX	ST	CEA	C Z		CNM	TUD	핕	SIN	UCL	ТНА	CC	F- IISB	UPU	2	TTV	LQAT	ICB
Architectures & system/module – integration for power	0																		
High power, high voltage, high current, silicon chips	8	1	1	3			1	1	N	1	N	2		N	N	1	N	N	
New 3D power semiconductors architectures	8	2	1	1			2	2	Ν	1	N	2		N	Ν	1	Ν	Ν	
System-on-Chip complex integration of Power devices, CMOS, and smart derivatives	10	1	1	1	2	2	3	1	2	N	3	1		N	N	N	3	N	
Power devices with true galvanic isolation	5	1	1	N	3	3	Ν		N	N	2	2		N	N	N	Ν	Ν	
Optimized blocks for Generic product structures: harvesting energy + energy management + energy storage + function + sensor/actuator + RF transmission		1	1	1	1	1	2	2	2	1	1	2		N	Ν	1	1	2	
Embedded software and algorithms for energy applications	5	Ν	3	N		Πľ	Ν	3	N	N		2		N	Ν	Ν	3	2	
Module integration for power modules	8	1	1	N	)	1	1	3	3	N		1		N	N	N	2	N	
Smart energy Areas of collaboration		IFX	ST	CEA	CNE	2	CNM	TUD	필	NIS	UCL	ТНА	CC	- <del>-</del>	UPU	2	TTV	LQAT	ICB
Methodology & tools	0																		
Mixed simulation tools covering electrical, mechanical, thermal, magnetic and optical strengths fields.	14	1	1	2	1	1	1	2	1	1	1	2		N	3	1	2	1	
Reliability aspects	11	1	1	N			1	2	2	1	1	1		N	2	1	3	N	
Verification tools	2	Ν	N	N			N	2	Ν	Ν	Ν	2		N	N	Ν	N	N	

# Equipment & Special Interest

Smart energy Areas of collaboration		IFX	H	ST	CEA	TND	CNM	TUD	1	SIN	UCL	ТНА	OCC	F- IISB	UPU	2	VTT	LQAT	8
Equipment ( to be consolidated in a later stage with equipment makers)	0																		
Equipment for new materials ( homo-hetero-localized Epitaxy, implantation, doping)	6	1		1	1		N		N	1	N	N		1	N	N	2	N	
Disruptive equipment technologies for thin and large wafers manufacturing, deep trenches, 3D power architectures	7	1		1	2	3	N		N	1	N	Ν		1	N	N	1	N	
Equipments for power 3D Wafer Level Packaging,	7	3	П	2	2	2	N		N	3	N	Ν		1	N	N	2	Ν	
Equipment for multi chip power Systems-in-Package: chip mounting, stacking characterization and complex testing (power + smart derivatives + RF)		3		2	N	1	3		N	N	N	2		3	N	N	1	N	

By F-IISB

#### Other suggested collaboration areas

Beyond equipment:

Energy and resource efficient manufacturing methods using smart idle mode and smart process flow planning and scheduling

By LQAT

#### Other suggested collaboration areas

Smart energy, Sensors

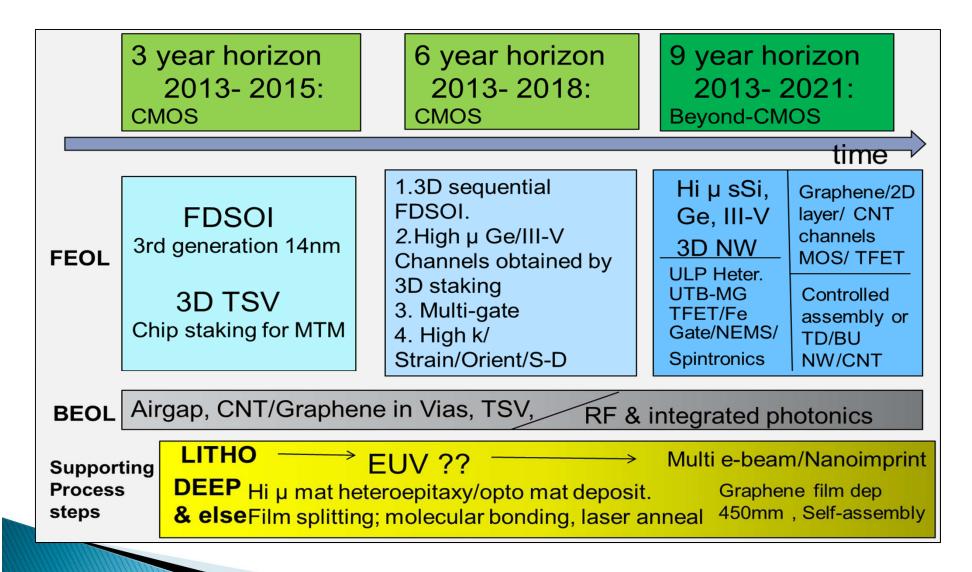
Power efficient communication devices (gateways, smart clients). Methods and test for interoperation between different technologies (e.g. PLC to WLAN, DSL)

# Long term strategic Programmes must be built-up based on:

- Joint technical roadmap addressing short, medium and long term horizon research
- Corresponding ecosystems (who is doing what)
- Excellence Centers
- Mechanisms of collaboration
- Routes of access



### Concrete cases-ie:nanoscale FET



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## NANOSCALE FET MULTI-YEARS PROGRAM

Integration Centric	Process centric							
Ultimate CMOS ST	<ul> <li>Novel Interconnect architecture IMEC</li> </ul>							
<ul> <li>3D Sequential integration CEA-Leti</li> </ul>	Ultimate processing ASM							
<ul> <li>Memories Micron</li> </ul>								
<ul> <li>Beyond CMOS Sinano</li> </ul>								
Horizon	tal activities							
<ul> <li>Equipment assessment</li> <li>Mechanisms of collaboration</li> <li>Routes of access</li> </ul>								
Ecosystems								

## Key targets ie : novel interconnects

#### 2014-2017

- New materials to meet conductivity requirements and reduce the dielectric permittivity
- Electrical, thermal, and mechanical reliability
- Three-dimensional control of interconnect features with it's associated metrology
- Modeling and characterization

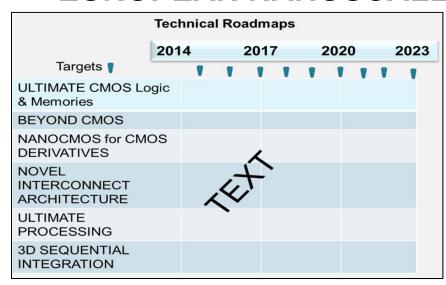
#### 2017-2020

- Low-κ dual damascene metal structures / air gap-Optical and RF interconnects,
   CNT/Graphene interconnects/via
- Identify solutions which address 3D structures and other packaging issues
- Modeling/characterization for new interconnects

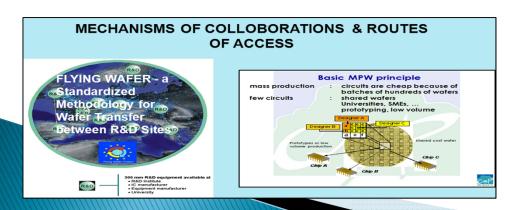
#### 2020-2023

- ▶ Ultra low-κ materials with κ<2.0 and to introduce air-gaps, the hybrid of low-κ materials and air-gaps could be the best solution.
- The TSV and 3D stacking technologies will also become of key importance.
- In order to replace Cu, other metals (Ag, silicides, ...), Nanowires, CNT, Graphene Nanoribbons, Topological insulators, Superconductors, and novel non-charge-based interconnects (Optical -interchip/intrachip, or Wireless

#### **EUROPEAN NANOSCALE-FET INFRASTRUCTURE**



COMPETENCES CENTERS R&D TOPICS								
MATERIALS	DEVICES ARCHITEC TURES	MODELING & SIMULATION	CHARACTE RIZATION & TEST	RELIABILITY	INTERCONN ECT & PACKAGING	EQUIPMENT ASSESMENT		



European Programmes of Common interest									
	3 year horizon 2013- 2015: CMOS	6 year horizon 2013- 2018: cmos	9 year horizon 2013- 2021: Beyond-CMOS						
time									
FEOL	FDSOI 3rd generation 14nm 3D TSV Chip staking for MTM	1.3D sequential FDSOI. 2.High µ Ge/III-V Channels obtained by 3D staking 3. Multi-gate 4. High k/ Strain/Orient/S-D	Hi µ sSi, Ge, III-V  3D NW ULP Heter. UTB-MG TFET/Fe Gate/NEMS/ Spintronics  Graphene/2D layer/ CNT channels MOS/ TFET Controlled assembly or TD/BU NW/CNT						
BEOL Airgap, CNT/Graphene in Vias, TSV, RF & integrated photonics									
Supporting Process steps  LITHO EUV ?? Multi e-beam/Nanoimprint DEEP Hi µ mat heteroepitaxy/opto mat deposit. Graphene film dep & elseFilm splitting; molecular bonding, laser anneal 450mm, Self-assembly									

ECOSYTEMS							
	P1	P2	P3	P4	P5		
	ULTIMATE CMO: (Logic & Memories)	BEYOND CMOS	NANO DEVICES FOR CMOS DERIVATIVE	NOVEL INTERCONNECTS ARCHITECTURES	ULTIMATE PROCESSING TECHNOLOGIES		
ACADEMICS	Tyndall FZ Julich FZ Julich FZ Julich FZ Julich FZ FZ Julich FZ FZ Julich FZ FZ Julich FZ F	Grenoble INP IUNET ILINET ILINET ILINE ILI	FZ Julich Grenoble INP IMEL IMEL IUME TUNNET Tyndall Uppsals Univ. Univ. Gransds ICN UNIV. Gransds URV URV KTH	TU Deift Tundali Grenobie INP FZJulist Uppsala Univ.	Uppsala Univ. Tyndail F2 Julich GME, SME SME ETH CNM CVT		
INSTITUTES	IMEC LETI FhG	IMEC LETI FhG	IMEC LETI FhG	IMEC LETI	IMEC LETI FhG		
INDUSTRIALIST	ST Thales Micron	ST Thales Micron	ST Infineon Thales	ST Thales	ST ASM		
	Intel	Microfi	Micron				



## Status and future deliverables (1/2)

### Intermediate report has been issued in May

available at <a href="http://www.aeneas-office.eu/web/nanoelectronics/Eni2.php">http://www.aeneas-office.eu/web/nanoelectronics/Eni2.php</a>

#### NanoscaleFET

Achieved: Detailed roadmaps/ecosystems long-term programme(LTP) structuration ongoing meeting oct. 1st

### Smart Energy

Achieved: Detailed content for roadmaps; 1<sup>st</sup> ecosystem identified

#### **Smart sensors**

Methodologie has been agreed. Consolidation ENI2/ Guardian Angels Nov. 20



## Status and future deliverables (2/2)

Heterogeneous Integration

Achieved: Detailed roadmaps/ecosystems

- System Integration Technology roadmap (tentative) Sept. WS LTP Nov
- Equipment and manufacturing

First draft proposing road mapping activities: July

### Other deliverables (Q4):

- Mechanisms of collaboration & Routes of access
- LTP governance
- Excellence centers

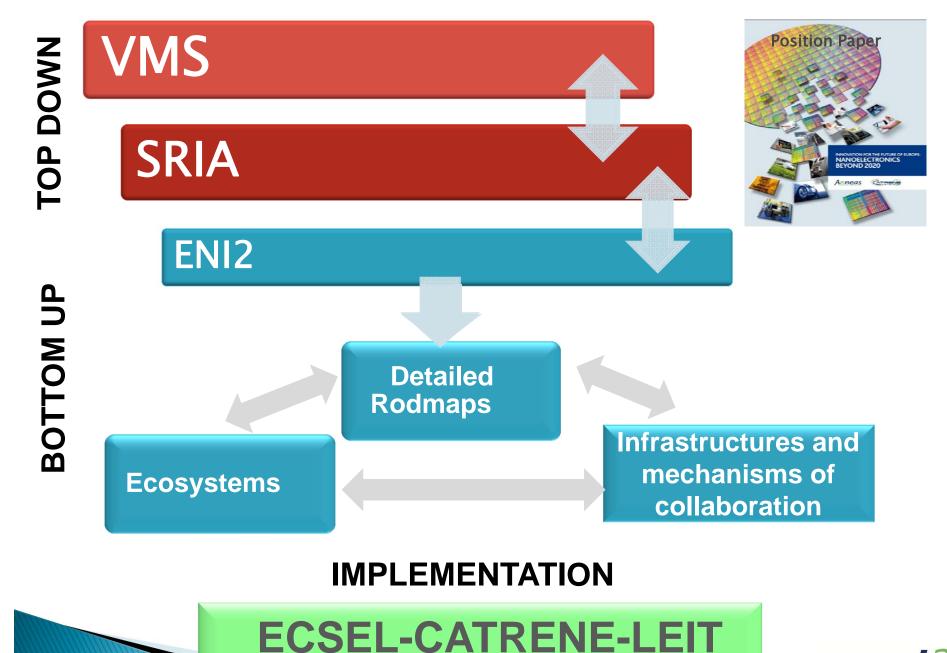
Final Report Dec. 2013



# ENI2 versus collaborative instruments

- ▶ ENI2 is a Framework of coordinated long-term activities serving as a basis for proposals in response to the calls to be launched by funding instruments (Horizon 2020, Catrene, ECSEL...)
- ▶ ENI2 could Contribute to the future Catrene White book (beyond 2015) and to the ECSEL MASP.....
- ENI2 collected and aligned inputs used in the update of the AENEAS/CATRENE VMS







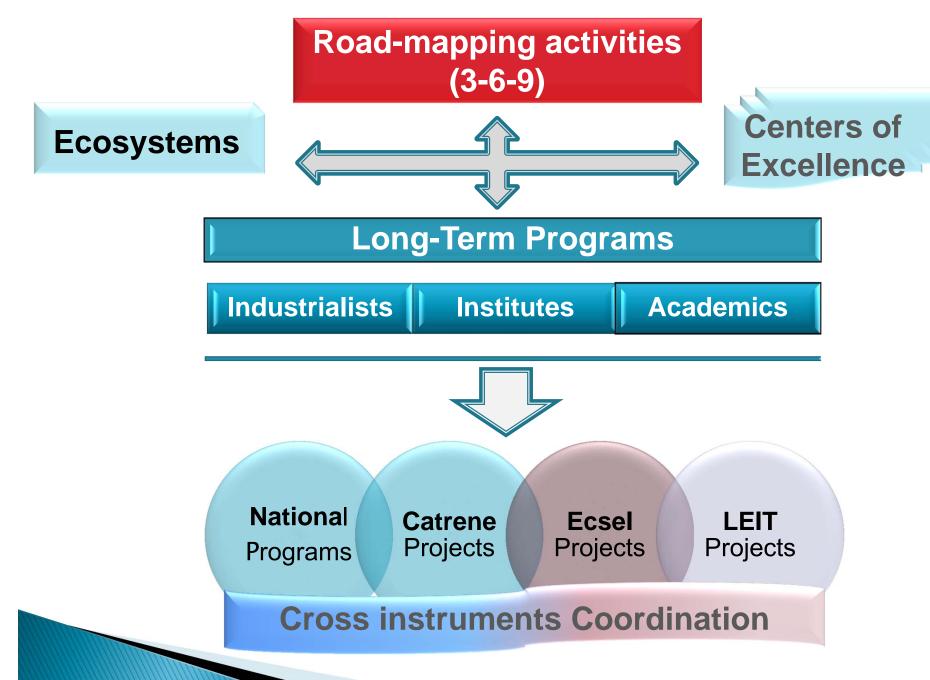
### ENI2 versus collaborative instruments

- The ENI2 partners have seen that it is required to work on ecosystems and roadmaps in a general not on funding oriented way.
- LEIT-CATRENE-ECSEL....They all have road mapping activities, but dedicated to their targets, interests.

## Support from PAs

- ENI2 is offering to the PAs a detailed shared vision of the technical priorities and associated targets to be pursued.
- The Strategic long term Programs will be submitted to the PAs for approval.
- Each Program will rely on a well identified ecosystem (who is doing what) reflecting the involvement of each Member State.
- ENI2 is delivering aligned content enabling long term funding support.





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